

THE CL055 (PNP) AND CL066 (NPN) ARE SILICON PLANAR EPITAXIAL COMPLEMENTARY PAIR SPECIALLY DESIGNED FOR 1-WATT AUDIO AMPLIFIER OUTPUT AND SWITCHING APPLICATIONS. THEY FEATURE LOW COLLECTOR-EMITTER KNEE VOLTAGE AND GOOD LINEARITY OF D.C. CURRENT GAIN.

CASE TO-92A



ABSOLUTE MAXIMUM RATINGS For p-n-p devices, voltage and current values are negative

Collector-Base Voltage	V _{CB0}	25V
Collector-Emitter Voltage	V _{CE0}	20V
Emitter-Base Voltage	V _{EB0}	5V
Collector Current	I _C	1A
Collector Peak Current (t ≤ 50ms)	I _{CM}	1.5A
Total Power Dissipation @ T _C ≤ 25°C	P _{tot}	1.5W
		625mW
Without Heat Sink @ T _A ≤ 25°C		
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to 150°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	V _{CB0}	25			V	I _C = 100μA I _E = 0
Collector-Emitter Breakdown Voltage	V _{CE0} *	20			V	I _C = 10mA I _B = 0
Collector-Emitter Cutoff Current	I _{CES}			0.5	μA	V _{CE} = 20V V _{BE} = 0
Emitter-Base Cutoff Current	I _{EB0}			1.0	μA	V _{EB} = 5V I _C = 0
Collector-Emitter Knee Voltage	V _{CEK}	0.25	0.5		V	I _C = 0.2A I _B = value at which I _C = 0.22A V _{CE} = 1V
Collector-Emitter Saturation Voltage	V _{CE(sat)} *	0.21	0.4		V	I _C = 0.5A I _B = 0.05A
Base-Emitter Voltage	V _{BE} *	0.87	1.2		V	I _C = 0.5A V _{CE} = 1V
D.C. Current Gain (Note)	HFE 1 *	50	160	360		I _C = 0.1A V _{CE} = 1V
	HFE 2 *	20	80			I _C = 1A V _{CE} = 2V
Current Gain-Bandwidth Product	f _T		120		MHz	I _C = 50mA V _{CE} = 10V

Note : HFE 1 is classified as follows. Group A : 50-100 Group B : 80-160
 Group C : 120-240 Group D : 180-360

* Pulse Test : Pulse Width = 0.3ms, Duty Cycle = 1%



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